## MICROWAVE POWER GAN HEMT

# TGI7179-130LHA

#### MICROWAVE SEMICONDUCTOR TECHNICAL DATA

## **FEATURES**

- **BROAD BAND INTERNALLY MATCHED HEMT**
- ·HIGH POWER

Pout= 51.0dBm at Pin= 43.5dBm

·HIGH GAIN

GL= 12.0dB at Pin= 20dBm

**LOW INTERMODULATION DISTORTION** 

IM3= -25dBc(Min.) at Pout= 44dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



## RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS= 40V IDSset= 0.8A f= 7.1 to 7.9GHz @Pin= 43.5dBm	dBm	50.0	51.0	_
Drain Current	IDS1		Α	_	7.0	9.0
Power Added Efficiency	ηadd		%	_	36	_
Linear Gain	GL	@Pin= 20dBm	dB	11.0	12.0	_
Gain flatness	ΔG		dB	_	_	±0.8
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 44dBm (Single Carrier Level) Δf= 5MHz (IM3) Δf= 150MHz (IM3-2)	dBc	-25	-30	_
	IM3-2		dBc	-25	-27	_
Drain Current	IDS2		А	_	_	5.0
Channel Temperature Rise *1	ΔTch		°C	_	120	140

## Recommended Gate Resistance(Rg): 10 $\Omega$

# **ELECTRICAL CHARACTERISTICS (Ta=25°C)**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 30mA	٧	-2.0	-3.0	-5.0
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	Α	_	20	_
Gate-Source Breakdown Voltage	VGSO	IGS= -25mA	٧	-10	_	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	0.8	1.0

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

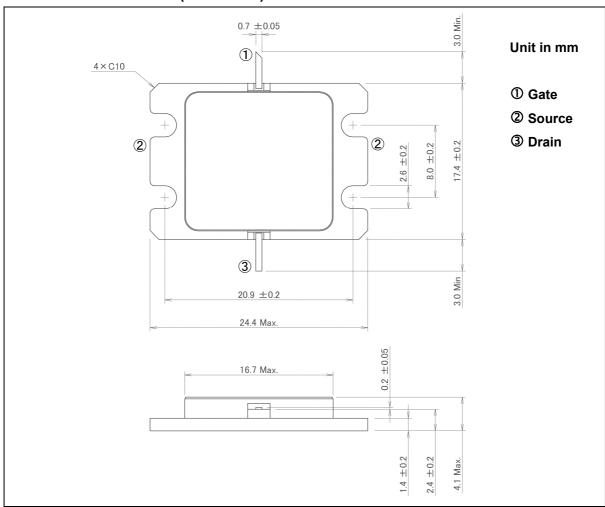
<sup>\*1:</sup>  $\Delta Tch = (VDS \times IDS2 + Pin(two-tone)) - Po(two-tone)) \times Rth(c-c)$ , calculated using parameters of IM3 test



## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	50
Gate-Source Voltage	VGS	V	-10
Drain Current	IDS	А	12
Total Power Dissipation (Tc= 25°C)	PT	W	200
Channel Temperature	Tch	°C	225
Storage Temperature	Tstg	°C	-65 to +175

## PACKAGE OUTLINE (7-AA06A)



## HANDLING PRECAUTIONS FOR PACKAGE MODEL

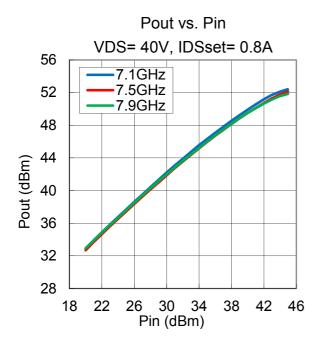
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

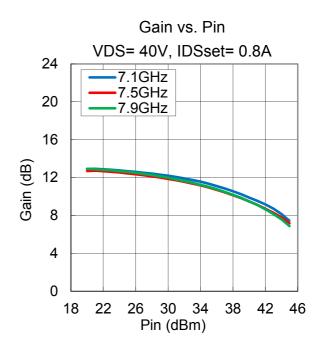


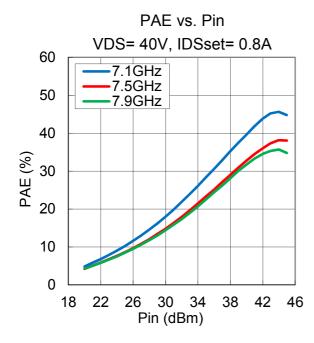
## TYPICAL RF PERFORMANCE

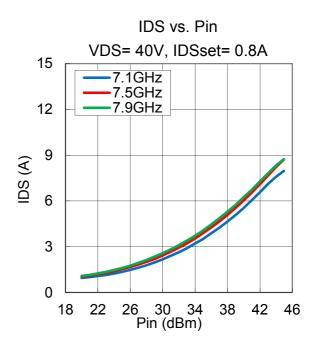
·Pout, Gain, PAE, IDS vs. Pin

VDS= 40V, IDSset= 0.8A, f= 7.1, 7.5, 7.9GHz, Ta= +25°C





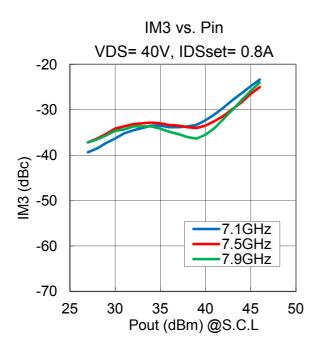


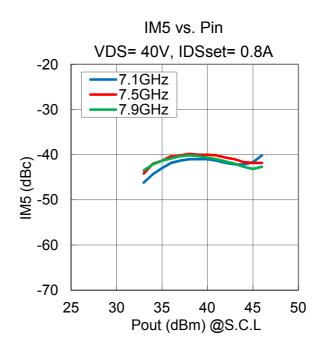




### ·IM3, IM5 vs Pout

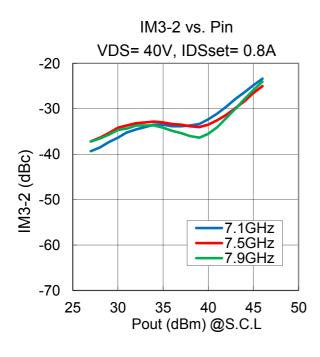
VDS= 40V, IDSset= 0.8A, f= 7.1, 7.5, 7.9GHz, Δf= 5MHz, Ta= +25°C

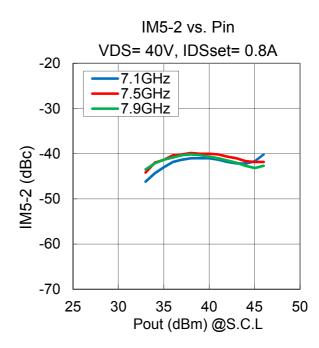




## ·IM3-2, IM5-2 vs Pout

VDS= 40V, IDSset= 0.8A, f= 7.1, 7.5, 7.9GHz, Δf= 150MHz, Ta= +25°C

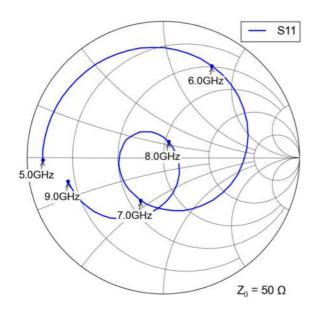


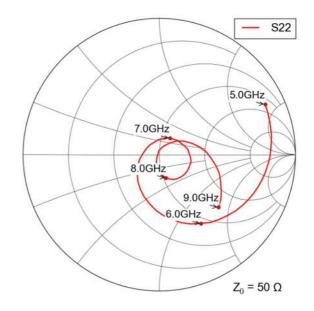


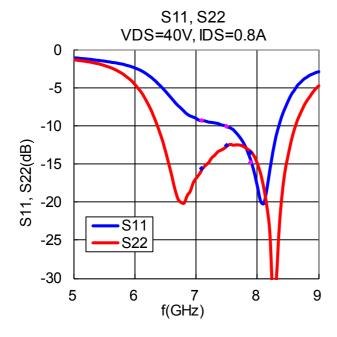


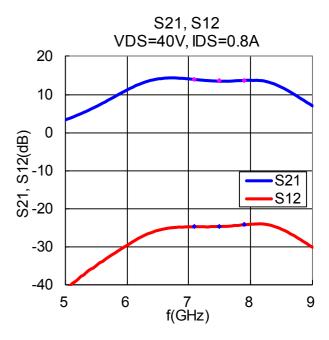
#### ·S-Parameters

VDS= 40 V, IDSset= 0.8 A, f= 5.0 to 9.0 GHz, Ta= +25  $^{\circ}$ C











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